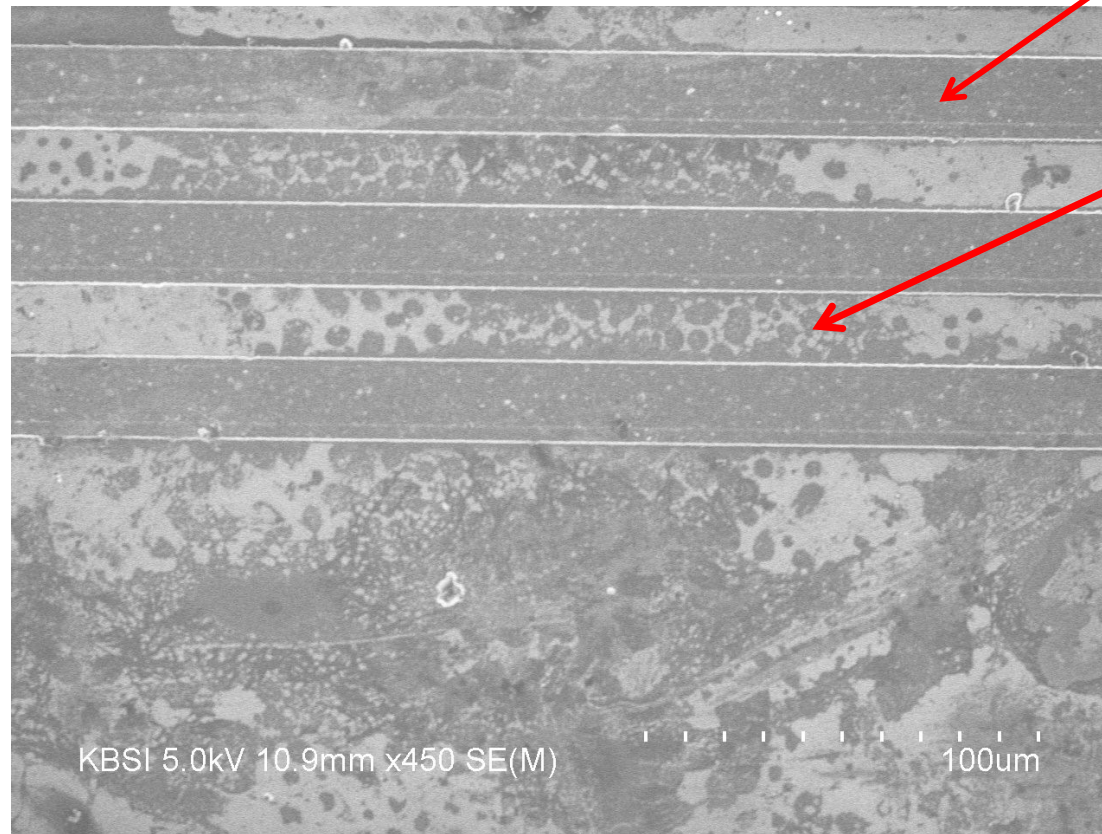


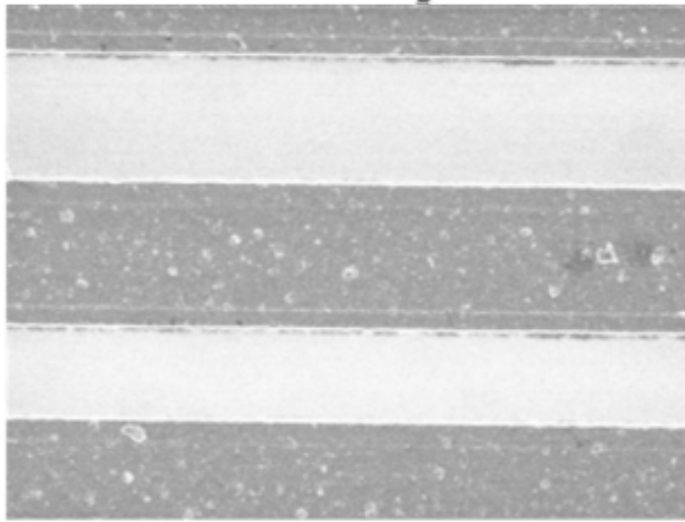
after DC bias sweeping up to 1000 V.

guard-ring electrode

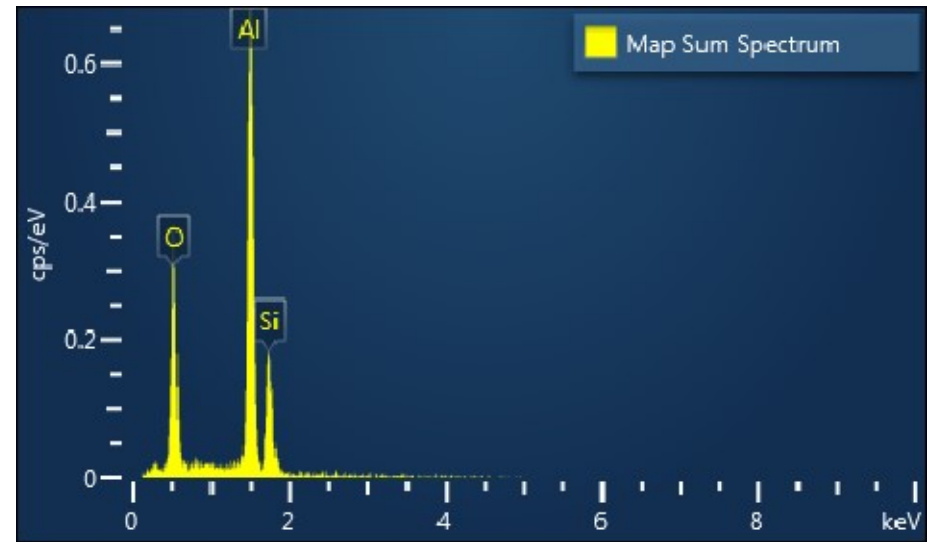
silicon oxide



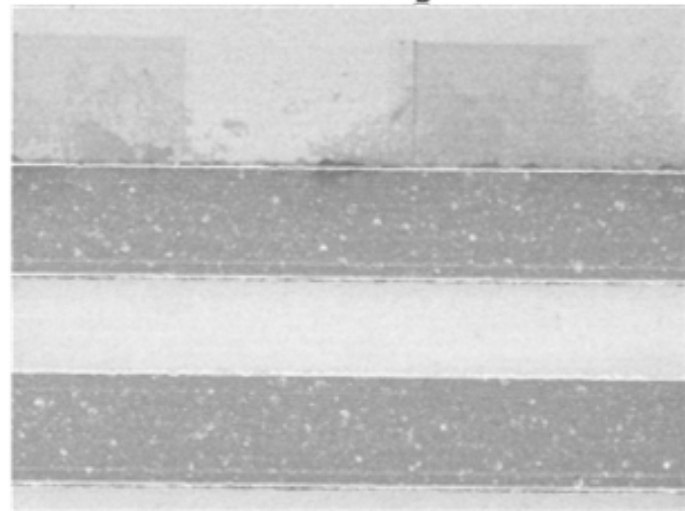
Electron Image 3



undamaged  
guard rings



Electron Image 4



HV-induced  
damage on  
guard rings.

